Serial No. 10/590,901

IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with <u>underlining</u> and deleted text with <u>strikethrough</u>.

Please REPLACE paragraph [0049], with the following paragraph:

[0049] In the next procedural step (Figure 8, reference symbol 81), the opening 42 for contacting the contact surface 20 of the power semiconductor component 2 is made in the insulating foil 4. A window 42 is opened. The window 42 is opened by the removal of material by laser ablation. For this purpose, a 002–002 laser with a wave length of 9.24 μ m is used. In this case, material is removed in such a way that a lateral surface 43 oriented at an angle to the contact surface 20 of the power semiconductor component 2, delimiting the opening 42 is obtained. A cleaning step is carried out after the removal of material in order to remove residues resulting from the said removal of material.